

1. Scope :

1-1. This specification applies to N channel silicon MOSFET chips,
device no. PM-0153

2. Structure :

2-1. Planar type .

2-2. Electrodes .

Source : Aluminum alloy .

Gate : Aluminum alloy .

Drain : Gold alloy

3. Size :

3-1. Chip size : 70.1 mils × 70.1 mils (1.780 mm × 1.780 mm).

3-2. Chip thickness : 12 ± 1.5 mils (0.305 ± 0.038 mm).

3-3. Pad size :

Source : 23.6 mils × 11.8 mils (0.600 mm × 0.300 mm).

Gate : 5.5 mils × 7.1 mils (0.140 mm × 0.180 mm).

3-4. Pattern drawing : Refer to the attached drawing.

4. Electrical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ $I_D = 1\text{mA}$	1.5	2.5	3.0	V
Gate to source leakage current	I_{GSS}	$V_{GS} = \pm 10\text{V}$ $V_{DS} = 0\text{V}$			± 1	μA
Drain to source leakage current	I_{DSS}	$V_{GS} = 0\text{V}$ $V_{DS} = 1500\text{V}$			1	μA
Drain to source on resistance	$R_{DS(on)}$	$V_{GS} = 5\text{V}$ $I_D = 25\text{mA}$		230	500	Ω
Diode forward voltage drop	V_{SD}	$V_{GS} = 0\text{V}$ $I_{SD} = 25\text{mA}$		1.00	1.8	V

Pattern drawing

